

SB5560S 55A SCRs

FEATURES

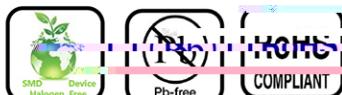
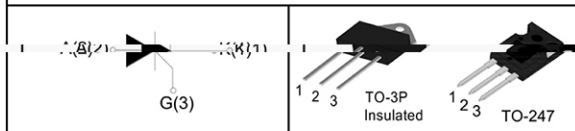
- High thermal cycling performance
- High voltage capacity
- Very high current surge capability

APPLICATIONS

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Parameters Summary

VD/VR:1200/1600V IT(RMS):55A IGT :60mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	value	Unit
Storage junction temperature range	T _{stg}	-40 ~ 150	°C
Operating junction temperature range	T _j	-40 ~ 125	°C
Repetitive peak off-state voltage (T = 25°C)	V _{DRM}	1200/1600	V
Repetitive peak reverse voltage (T = 25°C)	V _{RRM}	1200/1600	V
Non repetitive surge peak Off-state voltage	V _{DSS}	V _{DRM} + 100	V
Non repetitive peak reverse voltage	V _{RSM}	V _{RRM} + 100	V
RMS on-state current	I _{T(25°C)}	55	A
	I _{T(85°C)}	55	A
Non repetitive surge peak on-state current	I _{TSM}	550	A
Average on-state current (180° conduction angle)	I _{T(AV)}	55	A
I ² t value for fusing (tp=10ms)	I ² t	1500	A ² S
Critical rate of rise of on-state current (I = 2×IGT, tr ≤ 100 ns)	di/dt	150	A/μS
Peak gate current	I _{GM}	5	A
Average gate power dissipation	P _{G(AV)}	2	W

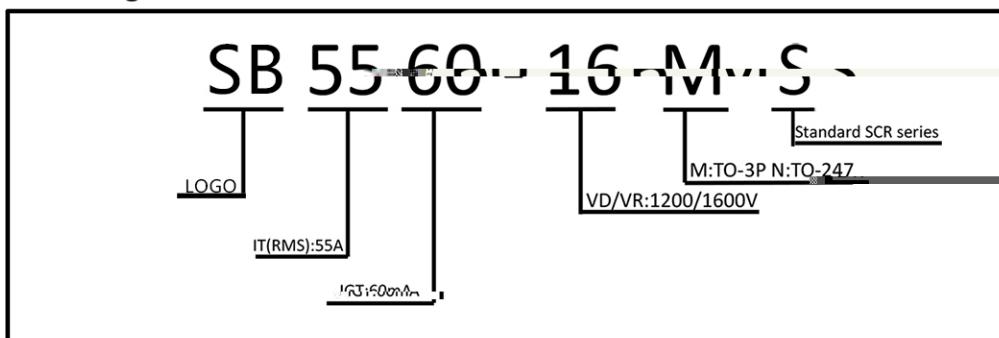
Thermal Resistances

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (DC)	TO-3P	0.65
		TO-247	0.60

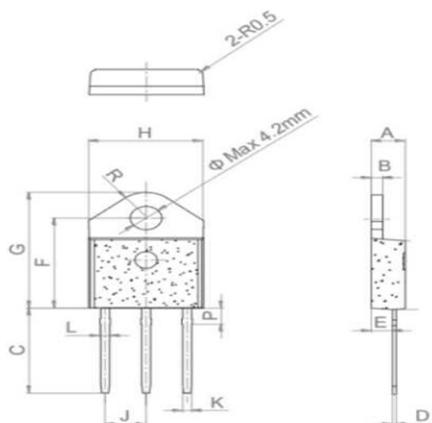
Symbol	Test Condition	MAX.	MIN.
I _{OT}	VD=V _{DRM} T _j =125°C	60	10
V _{GD}	VD=V _{DRM} T _j =125°C	1.2	0.8
I _T	I _G =1.2I _{OT}	MAX.	
I _H	I _G =1.2I _{OT}	MAX.	
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125°C	MIN.	

STATIC CHARACTERISTICS	
Symbol	Value (mA)
V _{TM}	I _G =500μA T _j =-500μS V _D =-25°C
I _{DRM}	V _D =V _{DDY} , V _G =V _{DDX}
I _{RRM}	V _D =V _{DDY} , V _G =V _{DDX}

Ordering Information

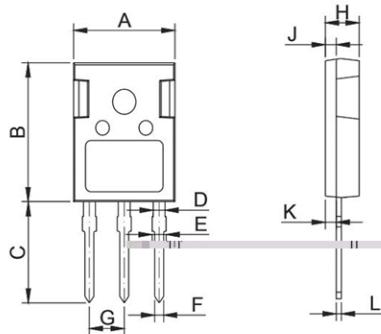


TO-3P Package Mechanical Data



Ref.	Dimensions	Units
A	1.50	mm
B	1.50	mm
C	1.50	mm
D	1.50	mm
E	0.50	mm
F	15.92	mm
G	16.32	mm
H	1.50	mm
I	1.50	mm
J	1.50	mm
K	1.50	mm
L	1.50	mm
P	3.08	mm
R	1.50	mm

TO-247 Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	15.90	0.610	0.622	0.634
B	20.80	21.00	22.20	0.810	0.822	0.834
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.07	0.070	0.074	0.081
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G		5.44			0.214	0.214
H		4.80	5.00	0.190	0.198	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031

FIG.1 Maximum power dissipation versus on-state current

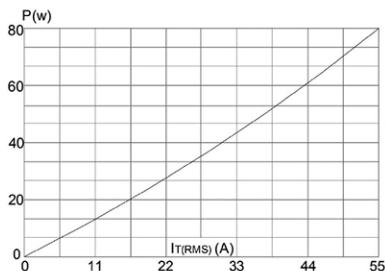


FIG.3: Surge peak on-state current versus number of cycles

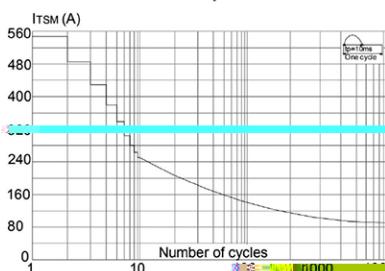


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of $I_2 t$

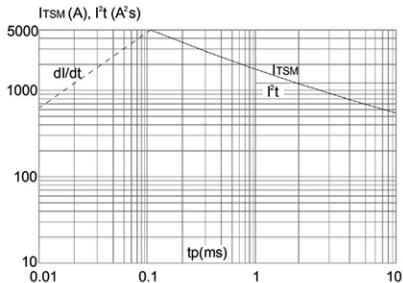


FIG.2: on-state current versus case temperature

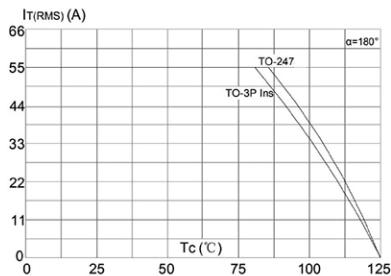


FIG.4: On-state characteristics (maximum values)

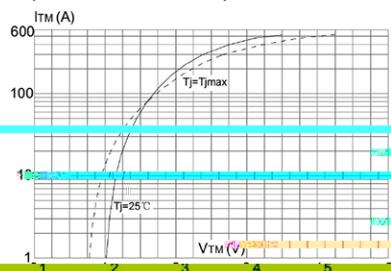


FIG.6: Relative variations of gate trigger current, inhibiting current and latching current versus junction temperature

